

Abstract of the Disclosure:

A reverse-blocking power semiconductor component includes a drift path subdivided into a source-side area and a drain-side area by a region with opposite doping. Provided above this region is a gate. Alternatively, the body zone of the one conduction type is subdivided into a source-side part and a drain-side part by a region of the other conduction type. This region acts as an electron collector. The reverse-blocking power semiconductor component can be incorporated in compensation components, and power transistors. Methods for producing power semiconductor components are also provided.

LDP/bb